



Revision 0.91

SINGLE FREQUENCY LASER DIODES Distributed Feedback Laser





General Product Information

Product	Application
785 nm DFB Laser	Raman Spectroscopy
with hermetic TO Package (RoHS compliant)	Metrology
including Monitor Diode	Interferometry

EYP-DFB-0785-00100-1500-TOV01-0000



Absolute Maximum Ratings

Parameter	Symbol	Unit	min	typ	max
Storage Temperature	T_S	°C	-40		85
Operational Temperature at Case	T_{C}	°C	-20		75
Operational Temperature at Laser Chip	T_{LD}	°C	0		50
Forward Current	I _F	mA			190
Reverse Voltage	V_R	V			2
Output Power	P_{opt}	mW			110
TEC Current	I _{TEC}	Α			1.0
TEC Voltage	V_{TEC}	V			1.0

Measurement Conditions / Comments

Stress in excess of one of the Absolute Maximum Ratings may damage the laser. Please note that a damaging optical power level may occur although the maximum current is not reached. These are stress ratings only, and functional operation at these or any other conditions beyond those indicated under Recommended Operational Conditions is not implied.

Recommended Operational Conditions

Parameter	Symbol	Unit	min	typ	max
Operational Temperature at Case	T_{case}	°C	-20		65
Operational Temperature at Laser Chip	T_{LD}	°C	15		40
Forward Current	I _F	mA			170
Output Power	P_{opt}	mW	20		100

Measurement Conditions / Comments
measured with integrating sphere

Characteristics at T_{LD} = 25° C at BOL

Parameter	Symbol	Unit	min	typ	max
Center Wavelength	λ_{C}	nm	784	785	786
Linewidth (FWHM)	$\Delta\lambda$	MHz		2	
Sidemode Supression Ratio	SMSR	dB		50	
Temperature Coefficient of Wavelength	dλ / dT	nm / K		0.06	
Current Coefficient of Wavelength	dλ / dI	nm / mA		0.003	

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Characteristics at T _{LD} = 25° (C at BOL				cont'd
Parameter	Symbol	Unit	min	typ	max
Laser Current @ P _{opt} = 100 mW	I _{LD}	mA			170
Slope Efficiency	η	W/A	0.6	0.8	1.4
Threshold Current	I _{th}	mA			70
Divergence parallel (FWHM)	$\Theta_{ }$	0		5	
Divergence perpendicular (FWHM)	Θ_{\perp}	0		18	
Degree of Polarization	DOP	%		80	

Measurement Conditions / Comments
parallel to Pin 1 - Pin 6 plane (see p. 3)
perpendicular to Pin 1 - Pin 6 plane (see p. 3)
$P_{opt} = 100 \text{ mW}$; E field perpendicular to Pin 1 - 6 plane

Symbol	Unit	min	typ	max
I _{mon} / P _{opt}	μΑ/mW	1	t.b.d.	100

∕leası	urement Conditions / Comments
$J_R =$	5 V

Symbol	Unit	min	typ	max
I _{TEC}	А		0.4	
U_TEC	V		0.4	
P _{loss}	W		0.4	
ΔΤ	K			40
	I _{TEC} U _{TEC} P _{loss}	I _{TEC} A U _{TEC} V P _{loss} W	I _{TEC} A U _{TEC} V P _{loss} W	I _{TEC} A 0.4 U _{TEC} V 0.4 P _{loss} W 0.4

Meası	rement Conditions / Comments
P _{opt} =	100 mW, ΔT = 20 K
P _{opt} =	100 mW, ΔT = 20 K
P _{opt} =	100 mW, ΔT = 20 K
P _{opt} =	100 mW, $\Delta T = Tcase - TLD $

Themistor (Standard NTC Ty)	p e)				
Parameter	Symbol	Unit	min	typ	max
Resistance	R	kΩ		10	
Beta Coefficient	β			3930	
Steinhart & Hart Coefficient A	А		1.029 x 10 ⁻³		
Steinhart & Hart Coefficient B	В		2.510 x 10 ⁻⁴		
Steinhart & Hart Coefficient C	C			1.051 x 10	-7

Measurement Conditions / Comments					
$T_{LD} = 25^{\circ} C$					
$R_1/R_2=e^{\beta(1/T_1-1/T_2)}$ at $T_{LD}=$	0° 50° C				
$1/T = A + B(\ln R) + C(\ln R)^3$					
T: temperature in Kelvin					
R: resistance at T in Ohm					

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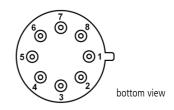


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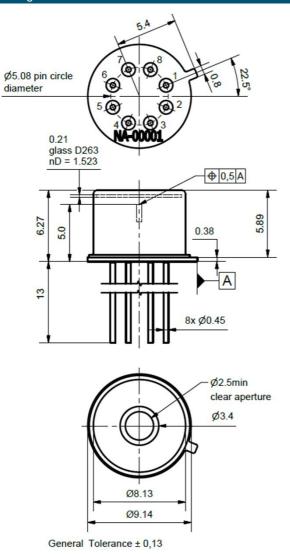
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Pi	n Assignment		
1	Laser Diode Anode	5	Thermistor
2	Laser Diode Cathode	6	Thermistor
3	Thermoelectric Cooler (-)	7	Photo Diode Anode
4	Thermoelectric Cooler (+)	8	Photo Diode Cathode
All	8 pins are isolated from case.		



Package Drawings



AIZ-19-0129-1426B

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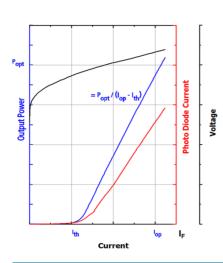
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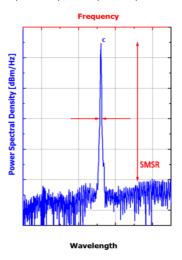


Typical Measurement Results

Output Power vs. Current



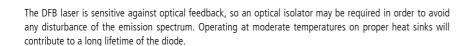
Spectra at Specified Optical Output Power



Performance figures, data and any illustrative material provided in this specification are typical and must be specifically confirmed in writing by eagleyard Photonics before they become applicable to any particular order or contract. In accordance with the eagleyard Photonics policy of continuous improvement specifications may change without notice.

Unpacking, Installation and Laser Safety

Unpacking the laser diodes should only be done at electrostatic safe workstations (EPA). Though protection against electro static discharge (ESD) is implemented in the laser package, charges may occur at surfaces. Please store this product in its original package at a dry, clean place until final use. During device installation, ESD protection has to be maintained.



Avoid direct and/or indirect exposure to the free running beam. Collimating and focussing the free running beam with optics as common in optical instruments will increase threat to the human eye.

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INVISIBLE LASER RADIATION
AVOID EYE OR SKIN EXPOSURE
TO DIRECT OR SCATTERED RADIATION
CLASS 4 LASER PRODUCT
WAVELENGTH 785 nm
MAX. OUTPUT POWER 110 mW



